

Isotropic Contact Properties in Monolayer GeAs Field-Effect Transistors

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Table S1. Lattice constants of ML GeAs and independent 2D metal electrodes (graphene, Ti₂CF₂, V₂CF₂, and Ti₃C₂O₂) and the Cu metal electrode.

	ML GeAs	graphene	Ti ₂ CF ₂	V ₂ CF ₂	Ti ₃ C ₂ O ₂	Cu
<i>a</i> (Å)	22.25	2.46	3.04	2.99	3.04	2.55
<i>b</i> (Å)	3.82	2.46	2.63	2.99	2.68	2.55